

said semiconductor film comprising a material selected from the group consisting of germanium and a germanium silicon alloy; and

irradiating the semiconductor film with a laser beam or a light having a strength equivalent to the laser beam to increase the degree of crystallinity of the semiconductor film.

38. (Twice Amended) A thin film transistor produced by a process comprising the steps of:

forming on a surface an intrinsic or substantially intrinsic semiconductor film having [an intrinsic or substantially intrinsic] a region to become a channel region containing therein oxygen at a concentration of 1×10^{19} atoms/cm³ or less, said semiconductor film comprising a material selected from the group consisting of germanium and a germanium silicon alloy; and

irradiating the semiconductor film with a laser beam or a light having a strength equivalent to the laser beam to increase the degree of crystallinity of the semiconductor film.

REMARKS

The Office Action of June 10, 1997 was received and carefully reviewed. Claims 23-38 are currently pending in the instant application.

Claims 23-38 remain rejected under the judicially created doctrine of obviousness type double patenting over claims 1-21 of U.S. Patent no. 5,313,075 and claims 1-14 of U.S. Patent No. 5,272,654. To overcome this rejection, Applicants intend to file a Terminal Disclaimer which will be filed by the undersigned as soon as it is received from Applicants. This should place this application in a condition for allowance.

In addition, claims 32, 36, 37 and 38 are amended herein to clarify the recited invention. Since these amendments merely clarify the invention

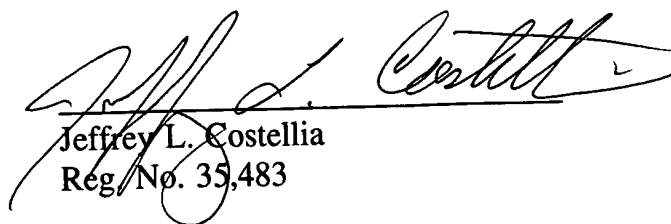
and do not raise any new issues for consideration in these claims, the amendments thereto should be considered acceptable after final rejection.

Specifically, claim 32 recites a step of forming a semiconductor film having an intrinsic or substantially intrinsic channel region and a step of irradiating the entire semiconductor film with a laser beam or a light. Applicants contend that the channel region may not be formed before the irradiating step because the channel region is defined by the ion implantation for source and drain regions and the ion implantation step is after the irradiating step in accordance with Example 1 of the instant application.

As a result, claims 32, 36, 37 and 38 are amended to merely clarify this point by reciting the formation of an intrinsic or substantially intrinsic semiconductor film having a region to "become" a channel region, since the channel region is not formed immediately on the surface, but instead occurs after the irradiation step. Consideration and allowance of these claims is now respectfully requested.

In view of the foregoing, it is respectfully requested that the rejections of record be reconsidered and withdrawn by the Examiner, that claims 23-38 be allowed and that the application be passed to issue. If the Examiner believes a conference would be of benefit in expediting the prosecution of the instant application, she is hereby invited to telephone counsel to arrange such a conference.

Respectfully submitted,



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